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Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 10559-586003	Application No. 10/802,991	
	sclosure Statement pplicant	Applicant Lawrence D. Wong		
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"Structural Change in Porous Silica Thin Film after Plasma Treatment"

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/Marianne L. Padgett/	10/16/2007
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Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

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(Use several si	heets if necessary)	Filing Date March 16, 2004	Group Art Unit: 1792	

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